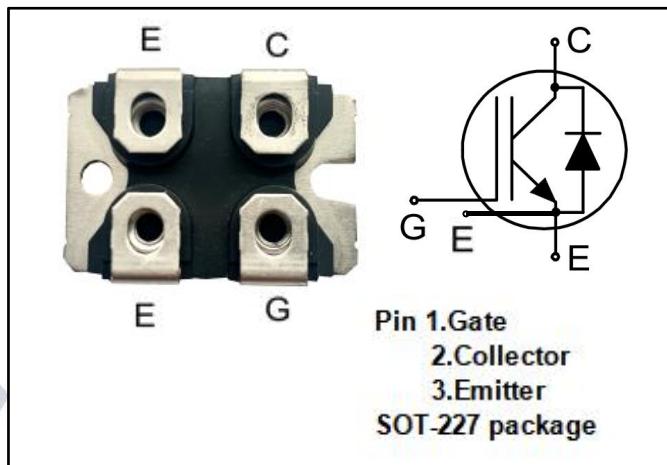


DESCRIPTION

- Low Saturation Voltage: $V_{CE}(\text{sat})=2.35\text{V}$ @ $I_C=110\text{A}$
- High Current Handling Capability
- High Power Density
- Short Circuit Capabilty

APPLICATIONS

- Synchronous Rectification in SMPS
- Power Inverters
- UPS,PFC
- High Frequency Power Inverters



ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current-Continuous @ $T_c=25^\circ\text{C}$	210	A
I_C	Collector Current-Continuous @ $T_c=110^\circ\text{C}$	110	A
I_{CM}	Pulsed Collector Current	470	A
I_F	Diode Forward Current @ $T_c=110^\circ\text{C}$	70	A
P_D	Power Dissipation , $T_c=25^\circ\text{C}$	750	W
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~175	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case IGBT	0.3	°C/W
R _{th j-c}	Thermal Resistance,Junction to Case Diode	0.45	°C/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0; I _C = 0.25mA	650	--	--	V
V _{GE(TH)}	Gate-Emitter Threshold Voltage	V _{GE} = V _{CE} ; I _C = 0.25mA	4.5	--	6.5	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 110A; V _{CE} = 15V, T _C =25°C	--	1.98	2.35	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 110A; V _{CE} = 15V, T _C =150°C	--	2.34	--	V
I _{GES}	Zero Gate Voltage Collector Current	V _{CE} =650V; V _{GE} =0	-	--	50	uA
I _{GES}	Zero Gate Voltage Collector Current	V _{CE} =650V; V _{GE} =0, T _C =150°C	-	--	3	mA
I _{GES}	Gate-Emitter Leakage Current	V _{GE} =±20V; V _{CE} =0	--	--	±100	nA
g _{ts}	Forward Transconductance	I _C = 60A; V _{CE} = 15V	--	42	--	S
C _{ies}	Input Capacitance	V _{GS} = 0V, V _{CS} = 25V, f = 1.0MHz	--	3722	--	pF
C _{oes}	Output Capacitance		--	460	--	
C _{res}	Reverse Transfer Capacitance		--	155	--	
Q _g	Total Gate Charge	V _{GE} = 15V, I _C = 110A, V _{CE} = 0.5V _{CES}	--	195	--	nC
Q _{gs}	Gate-Source Charge		--	40	--	
Q _{gd}	Gate-Drain Charge		--	80	--	

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$t_{d(on)}$	Turn-on Delay Time	$V_{GE} = 15V$, $I_C = 55A$, $V_{CE} = 400V$, $R_G = R_{off} = 2\Omega$ $T_J = 25^\circ C$	--	40	--	ns
t_r	Turn-on Rise Time		--	45	--	
E_{on}	Turn-on switching losses		--	2.5	--	mJ
$t_{d(off)}$	Turn-off Delay Time		--	150	--	ns
t_f	Turn-off Fall Time		--	30	--	
E_{off}	Turn-off switching losses		--	0.7	--	mJ
$t_{d(on)}$	Turn-on Delay Time	$V_{GE} = 15V$, $I_C = 55A$, $V_{CE} = 400V$, $R_G = R_{off} = 2\Omega$ $T_J = 150^\circ C$	--	35	--	ns
t_r	Turn-on Rise Time		--	42	--	ns
E_{on}	Turn-on switching losses		--	3.0	--	mJ
$t_{d(off)}$	Turn-off Delay Time		--	134	--	ns
t_f	Turn-off Fall Time		--	45	--	ns
E_{off}	Turn-off switching losses		--	0.87	--	mJ

REVERSE DIODE (FRED)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V_F	Diode Forward Voltage	$I_F = 100A; T_c = 25^\circ C$	--	1.9	2.4	V
V_F	Diode Forward Voltage	$I_F = 100A; T_c = 150^\circ C$	--	2.0	--	V
I_{RM}	Reverse recovery current	$V_R = 300V$: $I_F = 100A$; -diF/dt = 1500A/us $T_J = 150^\circ C$	--	95	--	A
t_{rr}	Reverse Recovery Time		--	110	--	ns

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